

500V Super-Junction Power MOSFET

FEATURES

- Very low FOM $R_{DS(on)} \times Q_g$
- 100% avalanche tested
- RoHS compliant

APPLICATIONS

- Switch Mode Power Supply (SMPS)
- Uninterruptible Power Supply (UPS)
- Power Factor Correction (PFC)

TO-220 GD S	TO-220F GDS	T0-251 G D S	TO-252
RoHS	TO-262 GDS	TO-263 GDS	

Device Marking and Package Information						
Device	TPP50R690C	TPA50R690C	TPU50R690C	TPD50R690C	TPC50R690C	TPB50R690C
Package	TO-220	TO-220F	TO-251	TO-252	TO-262	TO-263
Marking	50R690C	50R690C	50R690C	50R690C	50R690C	50R690C

Absolute Maximum Ratings $T_c = 25^{\circ}C$, unless otherwise noted					
_		Value			
Parameter	Symbol	TO-220,TO-251,TO-252 TO-262,TO-263	TO-220F	Unit	
Drain-Source Voltage (V _{GS} = 0V)	V _{DSS}	500		V	
Continuous Drain Current	I _D	4		А	
Pulsed Drain Current (note1)	I _{DM}	12		А	
Gate-Source Voltage	V _{GSS}	±30		V	
Single Pulse Avalanche Energy (note2)	E _{AS}	52.8		mJ	
Avalanche Current (note1)	I _{AR}	0.8		А	
Repetitive Avalanche Energy (note1)	E _{AR}	0.09		mJ	
Power Dissipation ($T_c = 25^{\circ}C$)	P _D	28	23	W	
Operating Junction and Storage Temperature Range	T _J , T _{stg}	-55~+150		°C	

Thermal Resistance					
		Value			
Parameter	Symbol	TO-220,TO-251,TO-252 TO-262,TO-263	TO-220F	Unit	
Thermal Resistance, Junction-to-Case	R _{thJC}	4.4	5.5	°C/W	
Thermal Resistance, Junction-to-Ambient	R _{thJA}	75	80	°C/W	

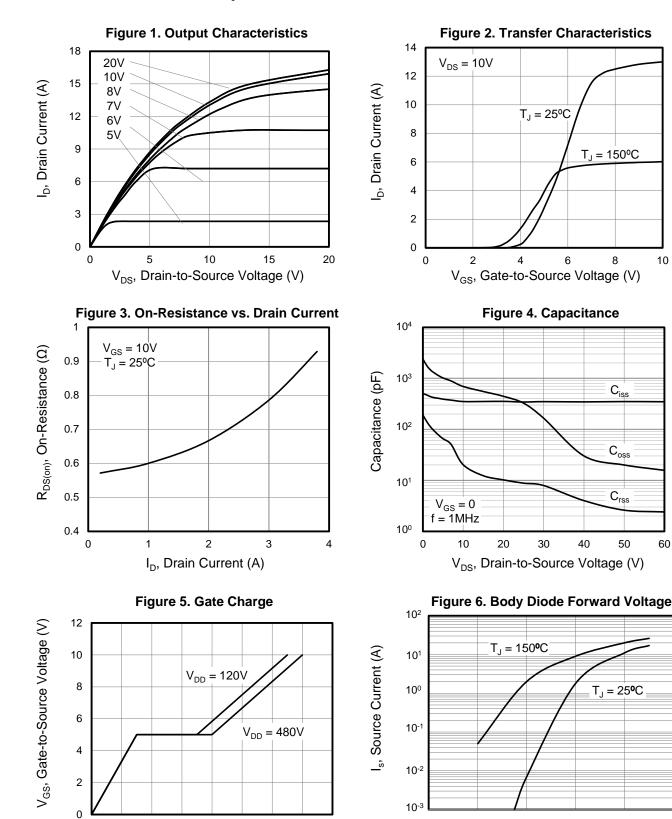


Specifications $T_J = 25^{\circ}C$, unless otherwise noted						
Parameter	Symbol	Symbol Test Conditions –	Value			Unit
Parameter			Min.	Тур.	Max.	Unit
Static						
Drain-Source Breakdown Voltage	V _{(BR)DSS}	$V_{GS} = 0V, I_{D} = 250 \mu A$	500			V
Zara Cata Valtaga Drain Current	1	$V_{DS} = 500V, V_{GS} = 0V, T_{J} = 25^{\circ}C$			1	
Zero Gate Voltage Drain Current	DSS	$V_{DS} = 500V, V_{GS} = 0V, T_{J} = 150^{\circ}C$			100	μA
Gate-Source Leakage	I _{GSS}	$V_{GS} = \pm 30 V$			±100	nA
Gate-Source Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_D = 250 \mu A$	2.5		4	V
Drain-Source On-Resistance (Note3)	$R_{DS(on)}$	V _{GS} = 10V, I _D = 1A		0.6	0.69	Ω
Forward Transconductance (Note3)	g _{fs}	V _{DS} = 10V, I _D = 1A		3		S
Dynamic						
Input Capacitance	C _{iss}	V _{GS} = 0V, V _{DS} = 50V, f = 1.0MHz		348		
Output Capacitance	C _{oss}			20		pF
Reverse Transfer Capacitance	C _{rss}			2.6		
Total Gate Charge	Q _g			8.6		nC
Gate-Source Charge	Q _{gs}	$V_{DD} = 400V, I_{D} = 4A, V_{GS} = 10V$		1.8		
Gate-Drain Charge	Q _{gd}			3.4		
Turn-on Delay Time	t _{d(on)}			36		
Turn-on Rise Time	t _r	V _{DD} = 400V, I _D = 4A,		27		
Turn-off Delay Time	t _{d(off)}	$R_{G} = 25\Omega$		79		ns
Turn-off Fall Time	t _f			29		
Drain-Source Body Diode Characteri	stics					
Continuous Body Diode Current	I _S	T 0500			4	۸
Pulsed Diode Forward Current	I _{SM}	$T_{\rm C} = 25^{\circ}{\rm C}$			12	A
Body Diode Voltage	V _{SD}	$T_J = 25^{\circ}C, I_{SD} = 4A, V_{GS} = 0V$		0.9	1.2	V
Reverse Recovery Time	t _{rr}			200		ns
Reverse Recovery Charge	Q _{rr}	$V_R = 400V, I_F = I_S,$ $di_F/dt = 100A/\mu s$		0.9		μC
Peak Reverse Recovery Current	l _{rrm}			8		А

Notes

- 1. Repetitive Rating: Pulse Width limited by maximum junction temperature
- 2. I_{AS} = 0.8A, V_{DD} = 50V, R_{G} = 25 Ω , Starting T_{J} = 25°C
- 3. Pulse Test: Pulse Width \leq 300µs, Duty Cycle \leq 1%





Typical Characteristics $T_J = 25^{\circ}C$, unless otherwise noted

1

1.2

50

60

10

2

0

1

3

4

Q_q, Total Gate Charge (nC)

5

6

7

8

0.2

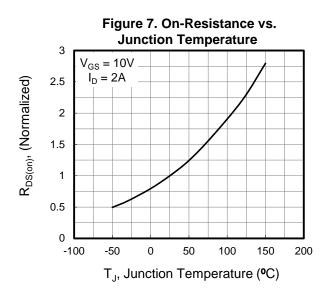
0.4

0.6

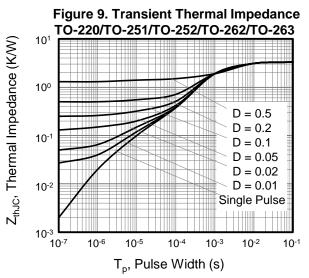
0.8

V_{SD}, Source-to-Drain Voltage (V)





Typical Characteristics $T_J = 25^{\circ}C$, unless otherwise noted



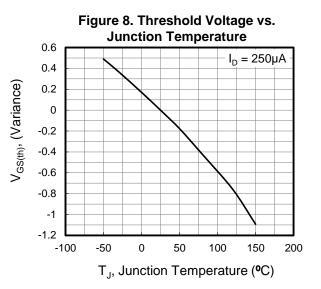
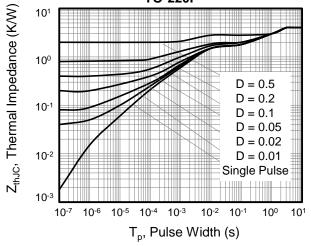
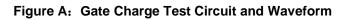


Figure 10. Transient Thermal Impedance TO-220F





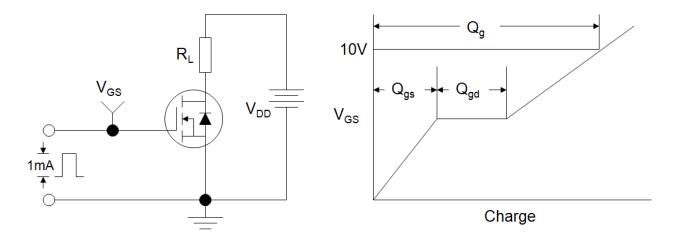


Figure B: Resistive Switching Test Circuit and Waveform

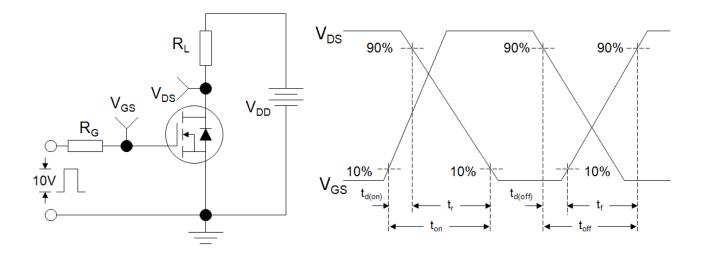
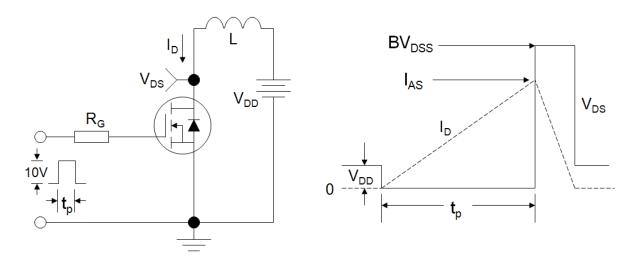
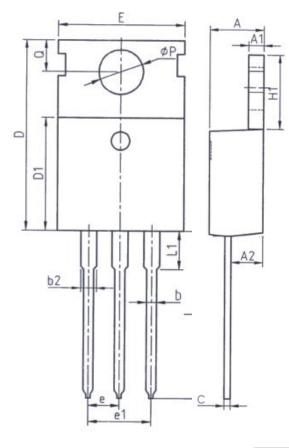


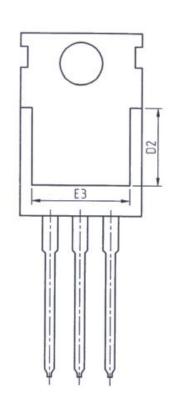
Figure C: Unclamped Inductive Switching Test Circuit and Waveform





TO-220

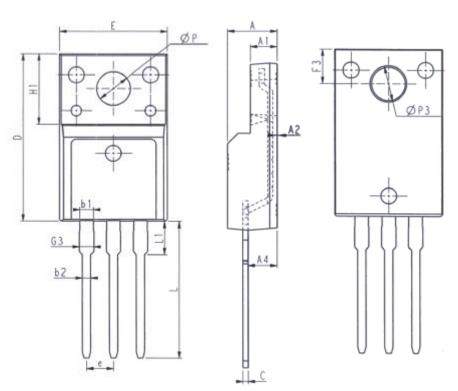




Unit: mm				
Symbol	Min.	Max.		
Α	4.37	4.77		
A1	1.25	1.45		
A2	2.20	2.60		
b	0.70	0.95		
b2	1.17	1.47		
с	0.40	0.65		
D	15.10	16.10		
D1	8.80	9.40		
D2	5.50	-		

Unit: mm				
Symbol	Min.	Max.		
E	9.70	10. 30		
E3	7.00	-		
e	2.54BSC			
e1	5. 08BSC			
H1	6. 25	6.85		
L	12.75	13.80		
L1	- 3.40			
Ρ	3. 40	3.80		
Q	2.60	3.00		



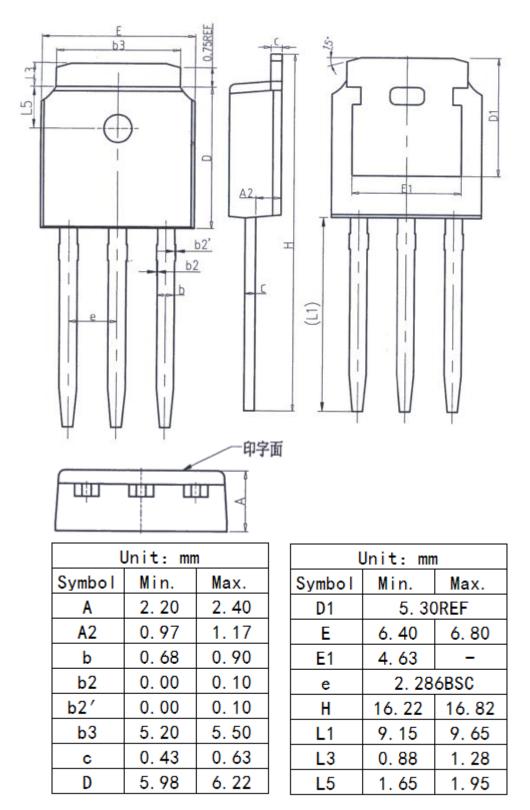


Unit: mm			l	Jnit: mm	1
Symbol	Min.	Max.	Symbol	Min.	Max.
E	9.96	10.36	L	12.68	13. 28
Α	4.50	4.90	L1	2.93	3.13
A1	2.34	2.74	Р	3.03	3. 38
A2	0.30	0.60	P3	3.15	3.65
A4	2.56	2.96	F3	3.15	3.45
с	0.40	0.65	G3	1.25	1.55
D	15. 57	16. 17	b1	1.18	1.43
H1	6. 70	DREF	b2	0.70	0.95
e	2. 54	4BSC			

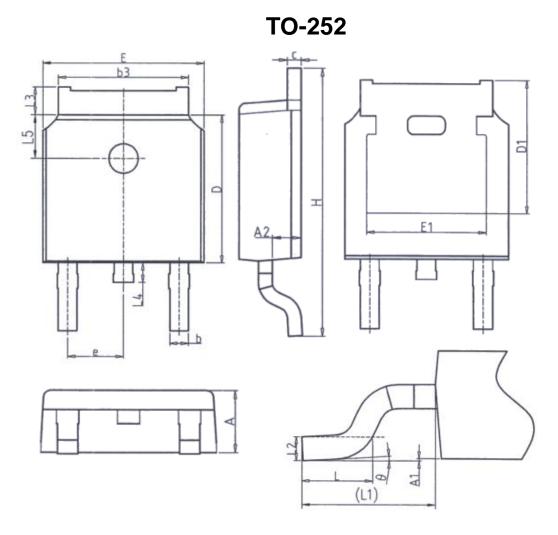
TO-220F









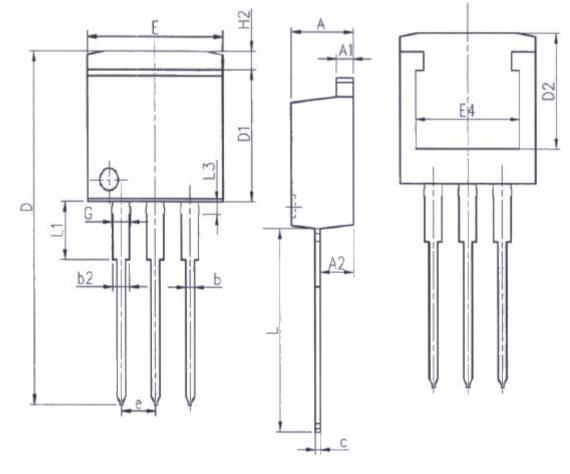


Unit: mm				
Symbol	Min.	Max.		
Α	2.20	2.40		
A1	0.00	0.20		
A2	0.97	1.17		
b	0.68	0.90		
b3	5.20	5.50		
с	0.43	0.63		
D	5.98	6. 22		
D1	D1 5. 30REF			
E	6.40	6.80		
E1	4.63	-		

Unit: mm				
Symbol	Min.	Max.		
e	2. 286BSC			
Н	9.40	10.50		
L	1.38	1.75		
L1	2.90REF			
L2	0, 51	BSC		
L3	0.88	1.28		
L4	-	1.00		
L5	1.65	1.95		
θ	0°	8°		



TO-262

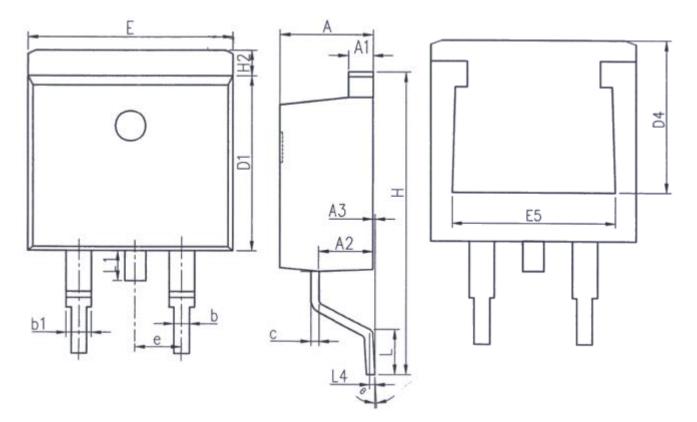


Unit: mm				
Symbol	Min.	Max.		
Α	4. 37	4.77		
A1	1.22	1.42		
A2	2. 47	2.87		
b	0.70	0.97		
b2	1.17	1.42		
с	0. 28	0.53		
D	23. 20	24. 02		
D1	8. 38	8.90		
D2	6.00	-		

Unit: mm					
Symbol	Min.	Max.			
E	9.90	10.39			
E 4	7.30	-			
e	2. 54BSC				
G	1.25	1.50			
H2	-	1.31			
L	13.34	14. 10			
L1	3.30	4.06			
L3	0.95	1.15			



TO-263



Unit: mm			Unit: mm		
Symbol	Min.	Max.	Symbol	Min.	Max.
Α	4. 37	4. 77	E	9.86	10.36
A1	1.22	1.42	E5	7.06	-
A2	2.49	2.89	e	2. 54BSC	
A3	0.00	0. 25	Н	14. 70	15.50
b	0.70	0.96	H2	1.07	1.47
b1	1.17	1.47	L	2.00	2.60
с	0.30	0.53	L1	1.40	1.70
D1	8.50	8.90	L4	0. 25BSC	
D4	6.60	-	θ	0°	9 °



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